

PBSS306PZ

100 V, 4.1 A PNP low VCEsat (BISS) transistor Rev. 3 — 26 July 2011

Product data sheet

1. **Product profile**

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS306NZ.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FF}) at high I_C
- High efficiency due to less heat generation
- Smaller Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-4.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-8.2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	56	80	mΩ



100 V, 4.1 A PNP low VCEsat (BISS) transistor

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		0.4
2	С	collector	4	2, 4
3	E	emitter		1—
4	С	collector	1 2 3	3
			SOT223 (SC-73)	sym028

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS306PZ	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS306PZ	S306PZ

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-100	V
V _{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-4.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-8.2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.7	W
			[3]	-	2	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

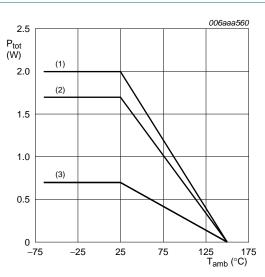
PBSS306PZ All information provided in this document is subject to legal disclaimers.

© Nexperia B.V. 2017. All rights reserved

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

^[3] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

100 V, 4.1 A PNP low VCEsat (BISS) transistor



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air [1] [2] [3]	<u>[1]</u>	-	-	179	K/W
	from junction to ambient		-	-	74	K/W	
	amblem		[3]	-	-	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

100 V, 4.1 A PNP low VCEsat (BISS) transistor

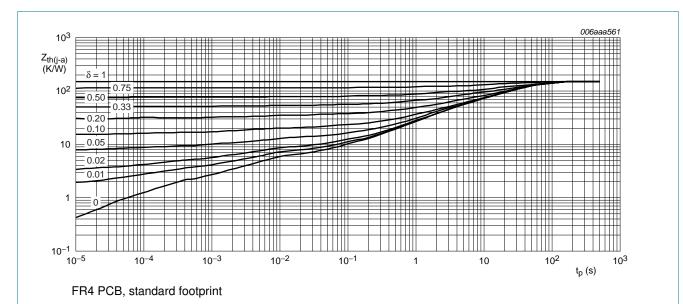


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

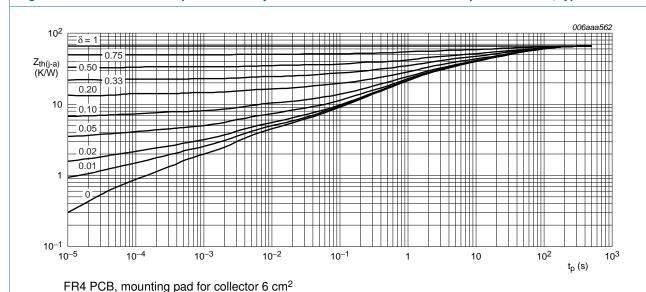
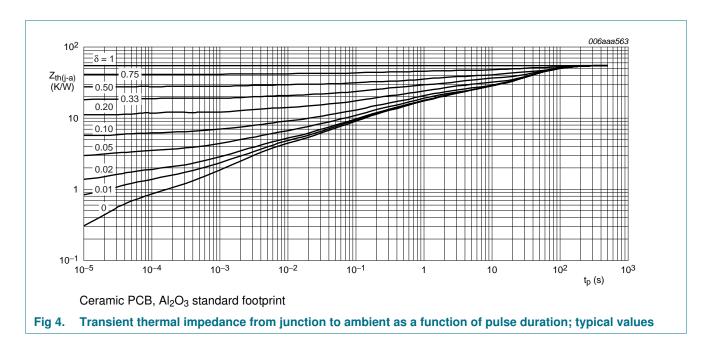


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

100 V, 4.1 A PNP low VCEsat (BISS) transistor



7. Characteristics

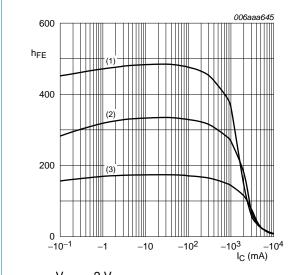
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -80 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C};$ $T_{amb} = 25 \text{ °C}$	-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V; } I_{C} = -0.5 \text{ A; pulsed;} $ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	200	300	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	150	260	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	100	175	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -4 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	25	40	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -0.5 \text{ A}; I_{B} = -50 \text{ mA}; \text{ pulsed};$ $t_{p} \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	-45	-65	mV
		$I_C = -1 \text{ A}; I_B = -50 \text{ mA}; \text{ pulsed};$ $t_p \le 300 \mu\text{s}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	-90	-130	mV
		$I_C = -4 \text{ A}$; $I_B = -400 \text{ mA}$; pulsed; $t_p \le 300 \text{ µs}$; $\delta \le 0.02$; $T_{amb} = 25 \text{ °C}$	-	-225	-320	mV
		I_{C} = -4.1 A; I_{B} = -410 mA; pulsed; $t_{p} \le 300 \mu\text{s}; \ \delta \le 0.02 ; T_{amb} = 25 ^{\circ}\text{C}$	-	-230	-325	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	56	80	mΩ
PBSS306PZ		All information provided in this document is subject to legal disclaimers.		© Nexne	eria B.V. 2017	All rights reserv

100 V, 4.1 A PNP low VCEsat (BISS) transistor

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.81	-0.9	V
		I_C = -4 A; I_B = -400 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.93	-1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.78	-0.85	V
t _d	delay time	$V_{CC} = -12.5 \text{ V}; I_{C} = -3 \text{ A}; I_{Bon} = -0.15 \text{ A};$ $I_{Boff} = 0.15 \text{ A}; T_{amb} = 25 \text{ °C}$	-	15	-	ns
t _r	rise time		-	185	-	ns
t _{on}	turn-on time		-	200	-	ns
ts	storage time		-	150	-	ns
t _f	fall time		-	175	-	ns
t _{off}	turn-off time		-	325	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ f = 100 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	100	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$	-	50	80	pF



 $V_{CE} = -2 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. DC current gain as a function of collector current; typical values

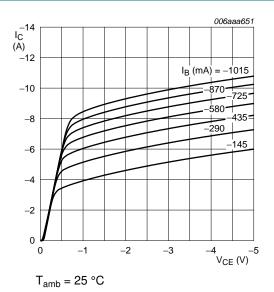
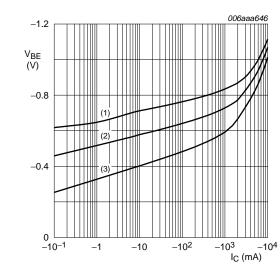


Fig 6. Collector current as a function of collector-emitter voltage; typical values

100 V, 4.1 A PNP low VCEsat (BISS) transistor



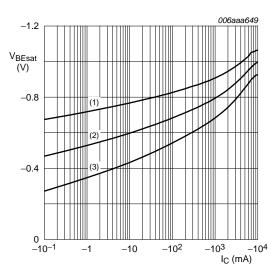
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, {}^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Base-emitter voltage as a function of collector current; typical values



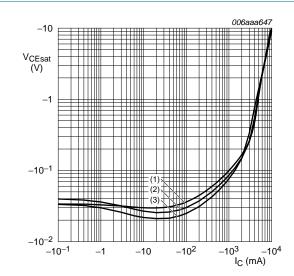
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



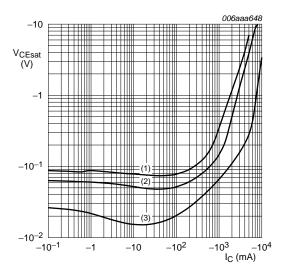
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

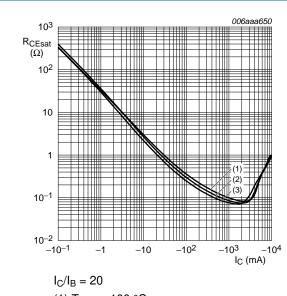
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

100 V, 4.1 A PNP low VCEsat (BISS) transistor

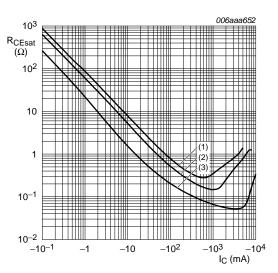


(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

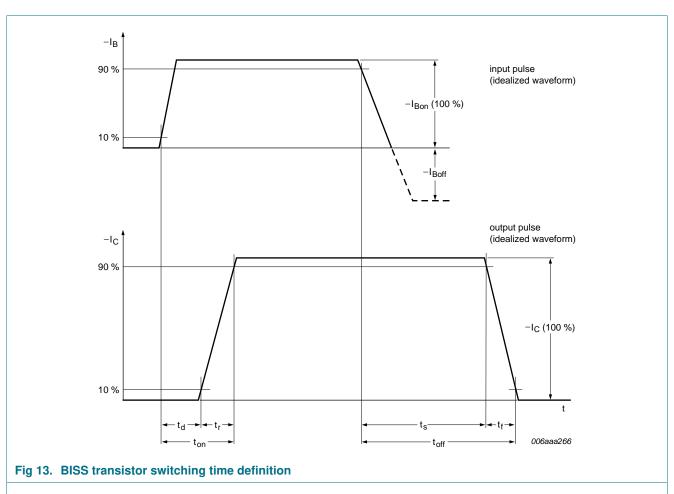
(2)
$$I_C/I_B = 50$$

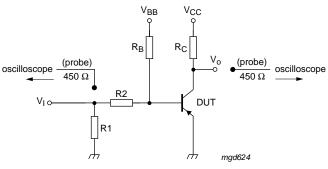
(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

100 V, 4.1 A PNP low VCEsat (BISS) transistor

8. Test information





 V_{CC} = -12.5 V; I_{C} = -3 A; I_{Bon} = -0.15 A; I_{Boff} = 0.15 A

Fig 14. Test circuit for switching times

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors and is suitable for use in automotive applications.

PBSS306PZ

All information provided in this document is subject to legal disclaimers.

9. Package outline

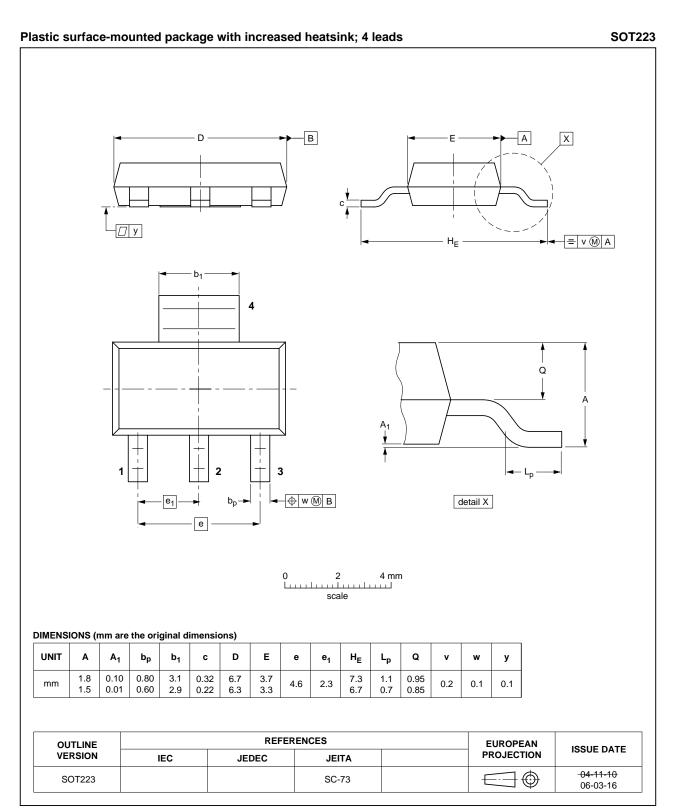
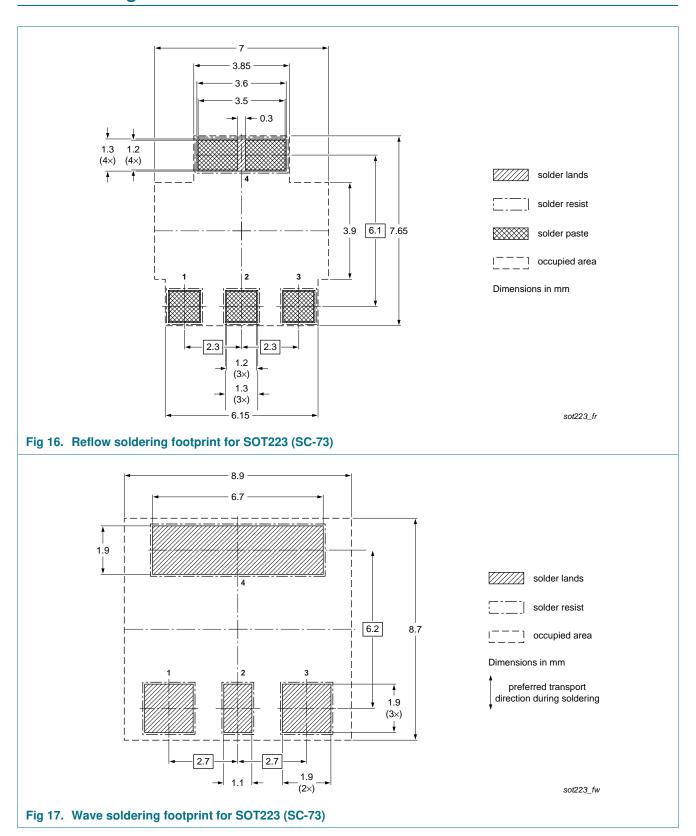


Fig 15. Package outline SOT223 (SC-73)

PBSS306PZ

100 V, 4.1 A PNP low VCEsat (BISS) transistor

10. Soldering



100 V, 4.1 A PNP low VCEsat (BISS) transistor

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS306PZ v.3	20110726	Product data sheet	-	PBSS306PZ v.2
Modifications:	• 1.2 "Features and			
	 In <u>7 "Characterist</u> 	ics" new parameter added	d, I _{CES}	
	 Fig 15. updated 			
	 12 "Legal informa 	<u>tion"</u> updated		
PBSS306PZ v.2	20091211	Product data sheet	-	PBSS306PZ v.1
PBSS306PZ v.1	20060920	Product data sheet	-	-

100 V, 4.1 A PNP low VCEsat (BISS) transistor

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

12.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nexperia.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective

PBSS306PZ

All information provided in this document is subject to legal disclaimers.

100 V, 4.1 A PNP low VCEsat (BISS) transistor

agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

100 V, 4.1 A PNP low VCEsat (BISS) transistor

14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	5
9	Package outline	.10
10	Soldering	. 11
11	Revision history	.12
12	Legal information	.13
12.1	Data sheet status	.13
12.2	Definitions	.13
12.3	Disclaimers	.13
12.4	Trademarks	.14
13	Contact information	14